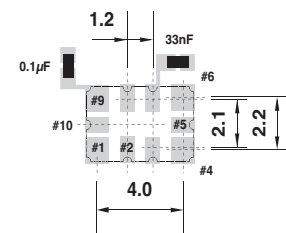
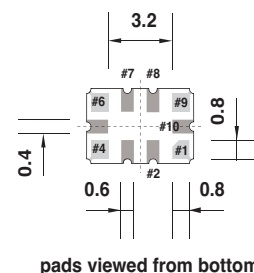
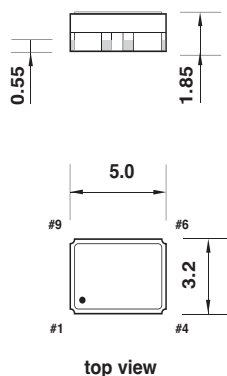


Type TL smd precision TCVCXO
High temperature, (10.0 ~ 52)MHz,
CMOS or clipped sine wave
(5.0 x 3.2)mm, height 1.85mm

A high quality, smd, TCVCXO manufactured over the frequency range of 10.0MHz to 52.0MHz
 $\pm 0.1\text{ppm}(-40 +85)^{\circ}\text{C}$, $\pm 0.2\text{ppm}(-40 +105)^{\circ}\text{C}$
 $+2.5\text{Vd.c.}$ or $+3.3\text{Vd.c.}$ supply
Tri-state enable disable, RoHS compliant

A standard package providing an excellent combination of parameters within a small enclosure.
Supplied on tape and reel with 1000 and 3000 pieces per reel.

Dimensions(mm)

pad connections:

- #1 V_{CON} : VCTCXO
NC: TCXO
- #2 NC
- #3 NC
- #4 ground
- #5 tri-state
- #6 F output
- #7 VC filter
- #8 NC
- #9 V_{DD}
- #10 ground

suggested land pattern
connect 0.1µF capacitor
between V_{DD} and ground

Frequency stability -vs- temperature:

TEMP. RANGE	COMBINED TOLERANCE - ppm					
$(-10 +60)^{\circ}\text{C}$	± 0.05	± 0.1	± 0.2	± 0.28	± 0.5	± 2.0
$(-20 +70)^{\circ}\text{C}$	± 0.05	± 0.1	± 0.2	± 0.28	± 0.5	± 2.0
$(-40 +85)^{\circ}\text{C}$	-	± 0.1	± 0.2	± 0.28	± 0.5	± 2.0
$(-40 +95)^{\circ}\text{C}$	-	-	± 0.2	± 0.28	± 0.5	± 2.0
$(-40 +105)^{\circ}\text{C}$	-	-	± 0.2	± 0.28	± 0.5	± 2.0

Tolerance inclusive of calibration tolerance at +25°C, temperature tolerance, load variation and supply voltage variation, first year ageing, vibration and shock

Electrical specification:

Parameter	2.5Vd.c.		3.3Vd.c.		Unit	
	min.	max.	min.	max.		
supply voltage(V_{DD}) variation	$V_{\text{DD}} -5\%$	$V_{\text{DD}} +5\%$	$V_{\text{DD}} -5\%$	$V_{\text{DD}} +5\%$	Vd.c.	
frequency range	10	52	10	52	MHz	
frequency tolerance @25°C	-	1.0	-	1.0	ppm	
frequency stability						
V_{s} supply voltage $\pm 5\%$	-	± 0.1	-	± 0.1	ppm	
V_{s} load $\pm 10\%$	-	± 0.05	-	± 0.05	ppm	
V_{s} aging first year	-	1.0	-	1.0	ppm	
OUTPUT WAVEFORM		CMOS				
supply current	10MHz ~ 38MHz	-	6.5	-	6.5	mA
	38MHz ~ 52MHz	-	7.5	-	7.5	mA
output level	output high	$90\%V_{\text{DD}}$	-	$90\%V_{\text{DD}}$	-	V
	output low	-	$10\%V_{\text{DD}}$	-	$10\%V_{\text{DD}}$	
transition time 10% ~ 90%	rise time	-	6.5	-	6.5	nano sec
	fall time	-	6.5	-	6.5	nano sec
duty cycle	45	55	45	55	%	
load	-	15	-	15	pF	
OUTPUT WAVEFORM		CLIPPED SINE WAVE				
supply current	10MHz ~ 38MHz	-	4.5	-	4.5	mA
	38MHz ~ 52MHz	-	5.0	-	5.0	mA
output level	0.8	-	0.8	-	Vp-p	
load	10KΩ//10pF		10KΩ//10pF			

Electrical specification:

Parameter		2.5Vd.c.		3.3Vd.c.		Unit
		min.	max.	min.	max.	
tri-state control	enable	80% V_{DD}	-	80% V_{DD}	-	V
	disable	-	20% V_{DD}	-	20% V_{DD}	
start up time		-	5	-	5	msec
control voltage range		0.5	2.5	0.5	2.5	V
pulling range		±5	-	±5	-	ppm
V_i input impedance (VTCXO)		100	-	100	-	k Ω
phase noise for TCXO V_{DD} 3.3V f_{out} 20MHz	100Hz offset	-122		-122		dBc/Hz
	1kHz offset	-142		-142		dBc/Hz
	10kHz offset	-154		-154		dBc/Hz
	100kHz offset	-157		-157		dBc/Hz
	1MHz offset	-159		-159		dBc/Hz

Ordering information:

EXAMPLE	type TL smd TCVCXO, 20.0MHz, ±5ppm trim range, +3.3Vd.c. supply, ±0.5ppm(-40 +85)°C, CMOS output
TFC PART NUMBER	TLA - 20.0M E A L J
TLA	type: TLA = TCVCXO type TL; (5.0 x 3.2)mm package, ±5ppm trim range
20.0M	frequency: 20.0MHz, frequency range (10.0 ~ 52.0)MHz
E	supply voltage: E = +3.3Vd.c.
A	frequency stability: A = ±0.5ppm
L	temperature range: L = (-40 +85)°C
J	output: J = CMOS/15pF
OPTIONS	
type	type: TLA = TCXO, TLT = TCXO
supply voltage	supply voltage: E = +3.3Vd.c., J = +2.5Vd.c.
frequency stability	frequency stability: Q = ±0.05ppm, B = ±0.1ppm, R = ±0.2ppm, K = ±0.28ppm, A = ±0.5ppm, C = ±2.0ppm
temperature range	temperature range: I = (-10 +60)°C, C = (-20 +70)°C, L = (-40 +85)°C, M = (-40 +95)°C, K = (-40 +105)°C
output	output: J = CMOS/15pF, S = clipped sine wave 10k Ω /10pF